

NCE N-Channel Enhancement Mode Power MOSFET

Description

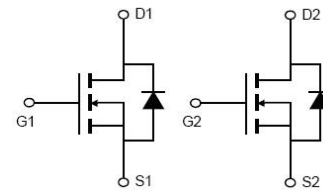
The NCE60ND03S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other switching application.

General Features

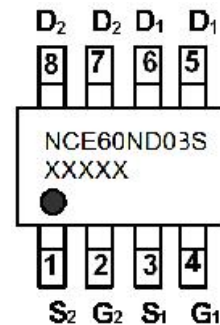
- $V_{DS} = 60V, I_D = 3A$
 $R_{DS(ON)} < 78m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 96m\Omega @ V_{GS} = 4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

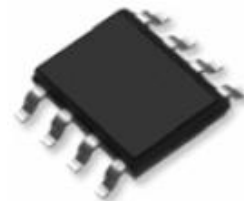
- Battery switch
- DC/DC converter



Schematic diagram



Marking and pin Assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
60ND03S	NCE60ND03S	SOP-8	-	-	-

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	3	A
Drain Current-Pulsed (Note 1)	I_{DM}	10	A
Maximum Power Dissipation	P_D	1.7	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	73.5	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						

Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	65	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.8	1.3	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A	-	68	78	mΩ
		V _{GS} =4.5V, I _D =3A	-	80	96	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3A	4	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	510	-	PF
Output Capacitance	C _{oss}		-	34	-	PF
Reverse Transfer Capacitance	C _{rss}		-	26	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =3A V _{GS} =10V, R _{GEN} =1Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =3A, V _{GS} =10V	-	14.6	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	nC
Gate-Drain Charge	Q _{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

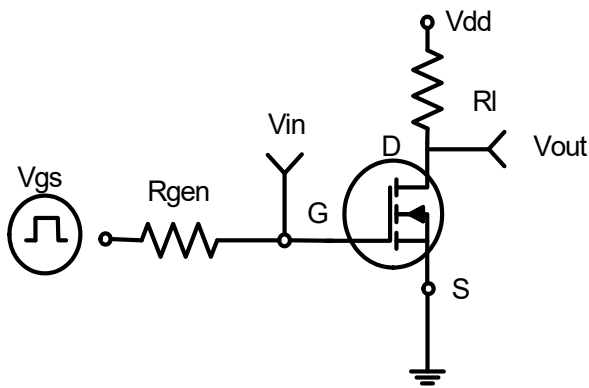


Figure 1: Switching Test Circuit

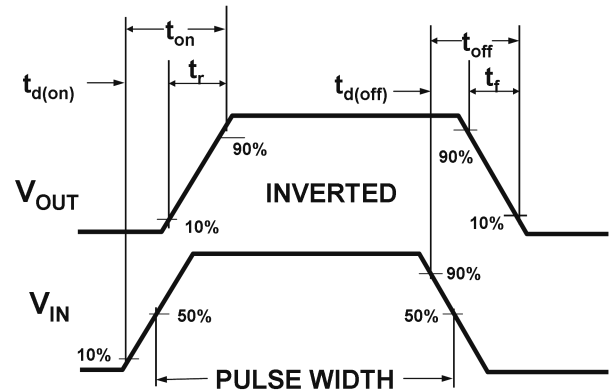


Figure 2: Switching Waveforms

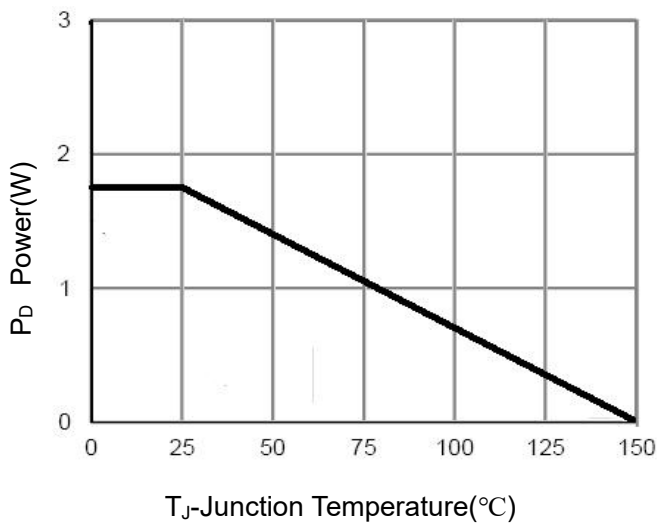


Figure 3 Power Dissipation

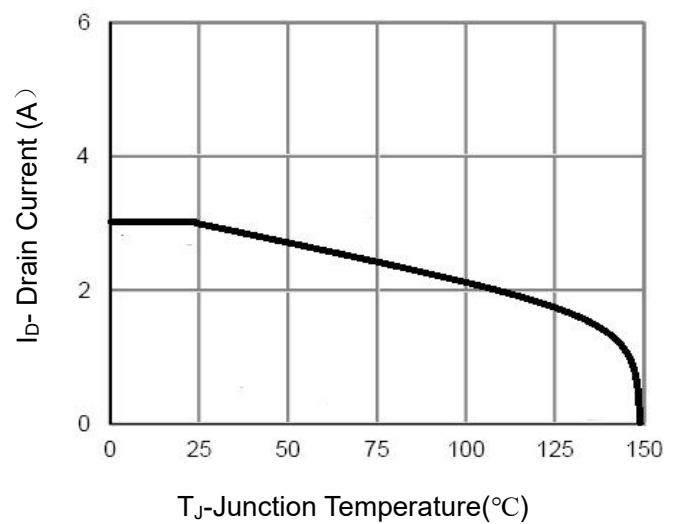


Figure 4 Drain Current

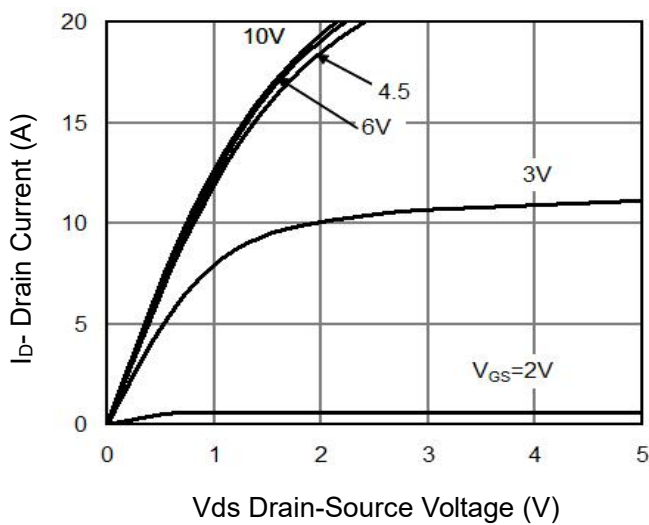


Figure 5 Output Characteristics

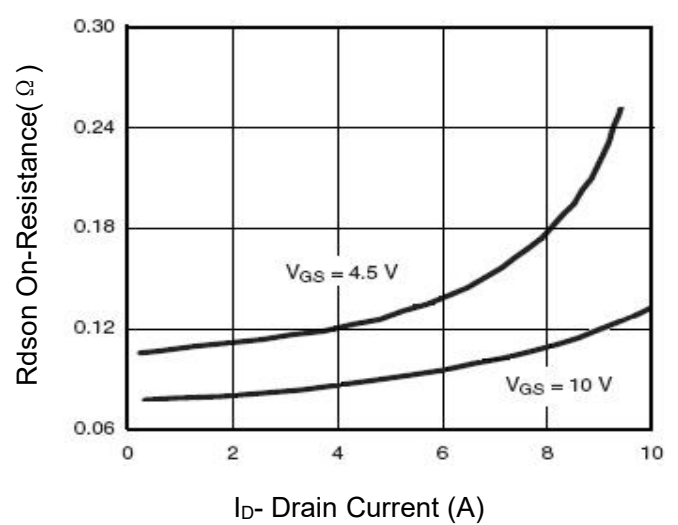


Figure 6 Drain-Source On-Resistance

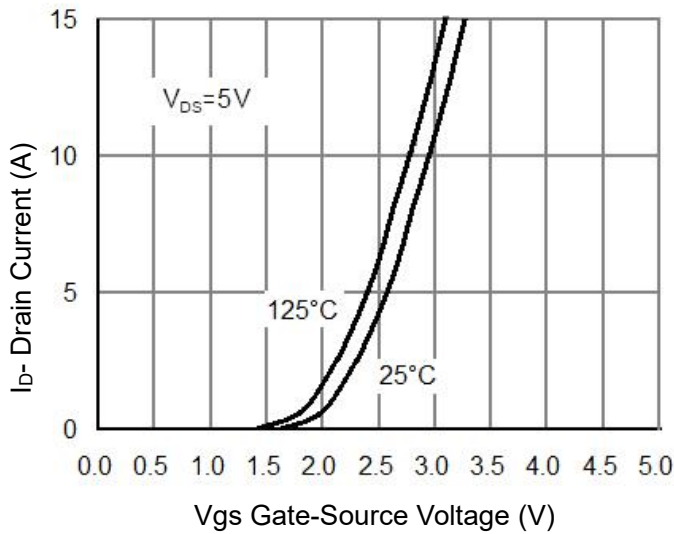


Figure 7 Transfer Characteristics

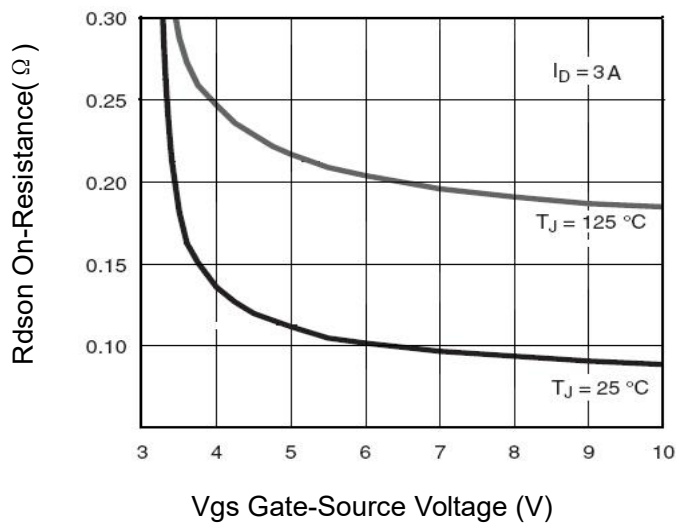


Figure 9 $R_{DS(on)}$ vs V_{GS}

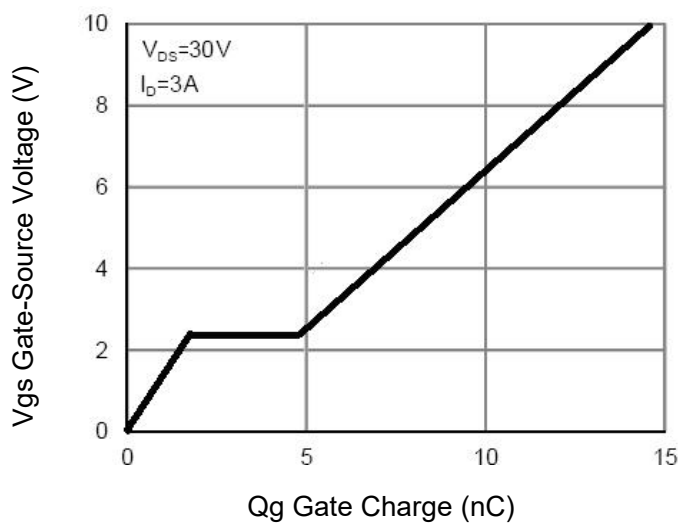


Figure 11 Gate Charge

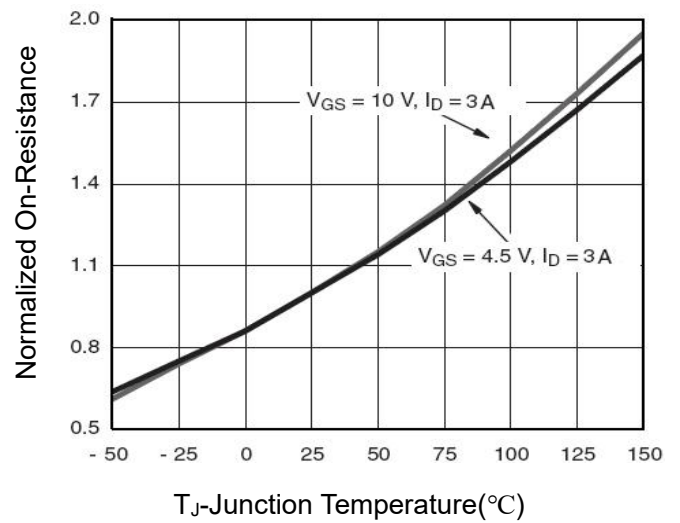


Figure 8 Drain-Source On-Resistance

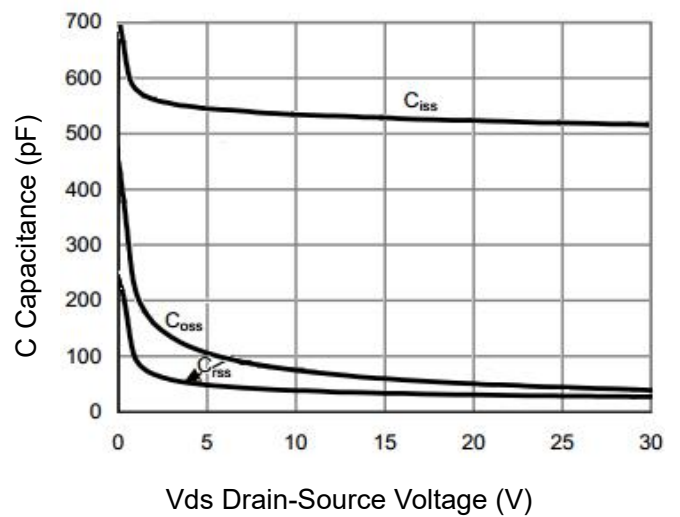


Figure 10 Capacitance vs V_{DS}

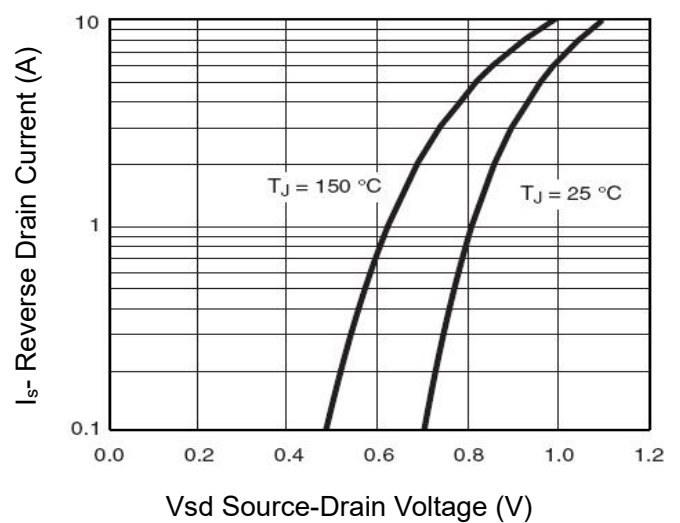


Figure 12 Source- Drain Diode Forward

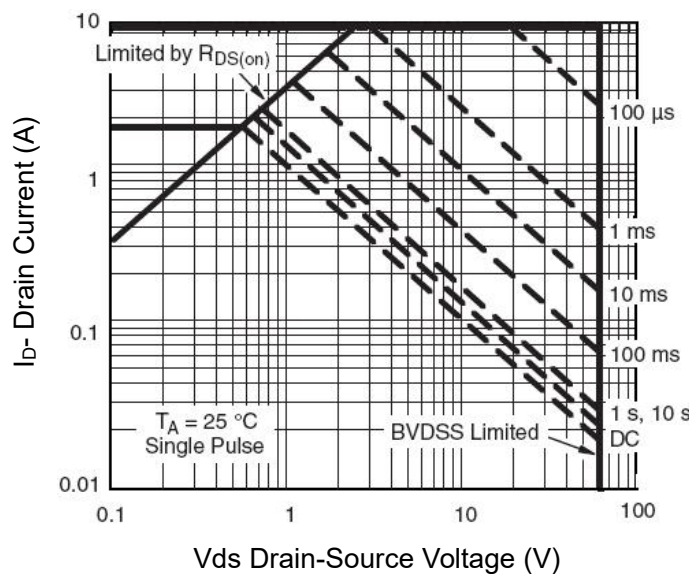


Figure 13 Safe Operation Area

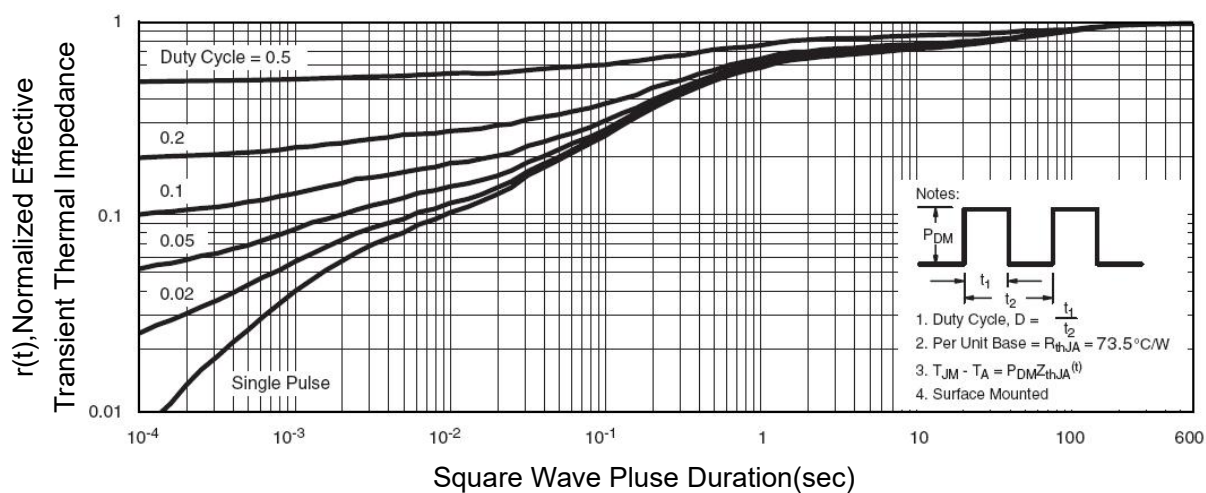
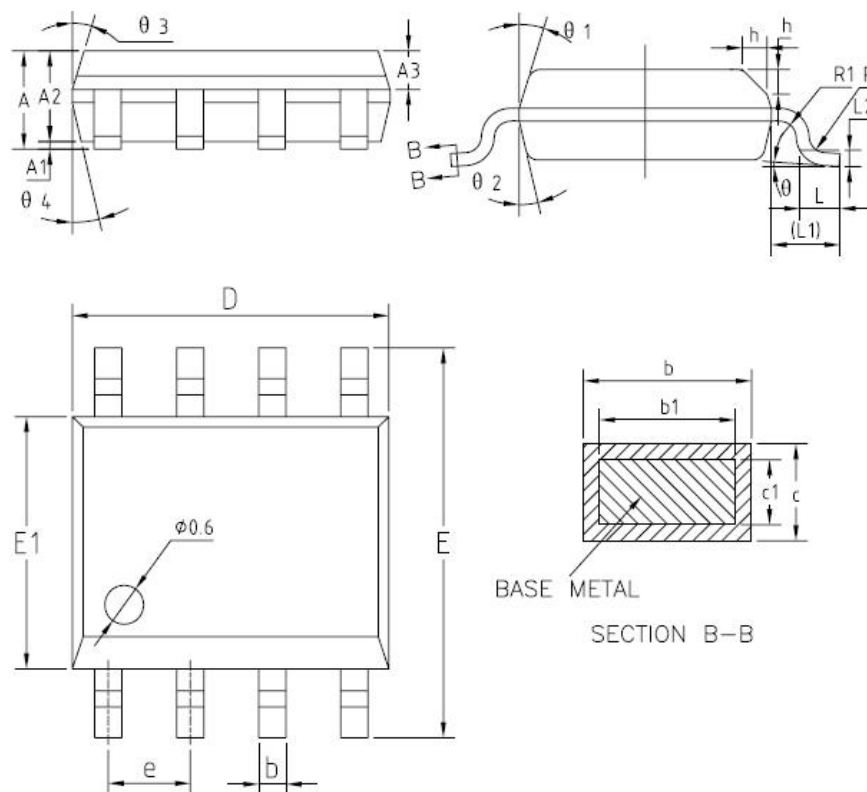


Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.15	0.25
A2	1.25	1.40	1.65
A3	0.50	0.60	0.70
b	0.38	—	0.51
b1	0.37	0.42	0.47
c	0.18	—	0.25
c1	0.17	0.20	0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.17	1.27	1.37
L	0.45	0.60	0.80
L1	1.04REF		
L2	0.25BSC		
R	0.07	—	—
R1	0.07	—	—
h	0.30	0.40	0.50
θ	0°	—	8°
θ_1	15°	17°	19°
θ_2	11°	13°	15°
θ_3	15°	17°	19°
θ_4	11°	13°	15°

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